

BC859

Rev.E Mar.-2016

描述 / Descriptions

SOT-23 塑封封装 PNP 半导体三极管。Silicon PNP transistor in a SOT-23 Plastic Package.

特征 / Features

高电流增益, 低 $V_{CE(sat)}$.

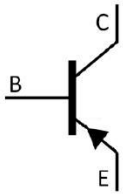
High current gain, Low collector-emitter saturation voltage.

用途 / Applications

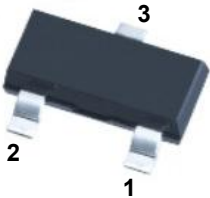
用于一般放大

General power amplifier application.

内部等效电路 / Equivalent Circuit



引脚排列 / Pinning



PIN1 : Emitter

PIN 2 : Base

PIN 3 : Collector

放大及印章代码 / h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	A	B
h_{FE} Range	125~250	220~475
Marking	H4A	H4B

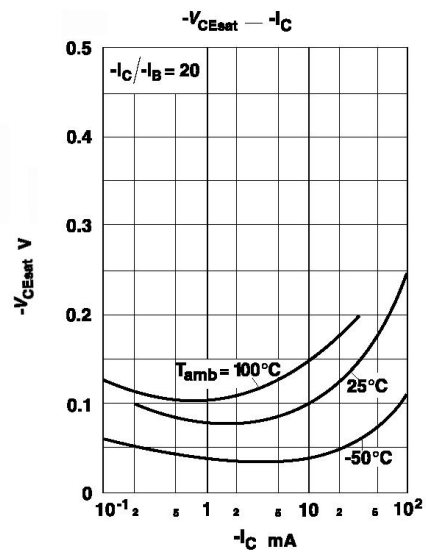
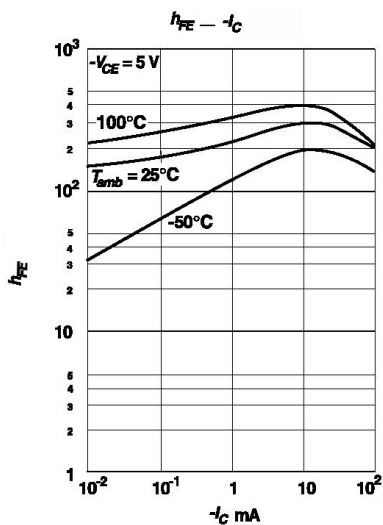
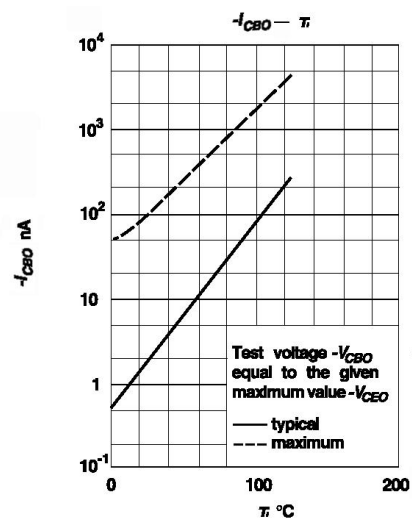
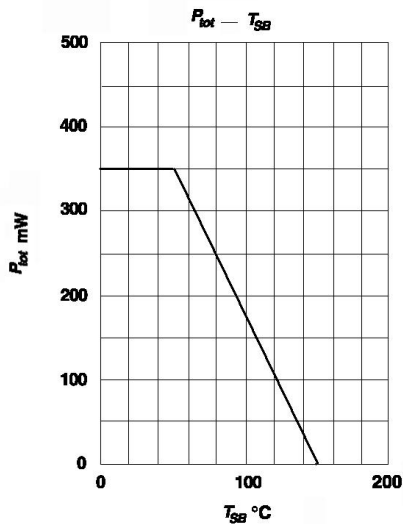
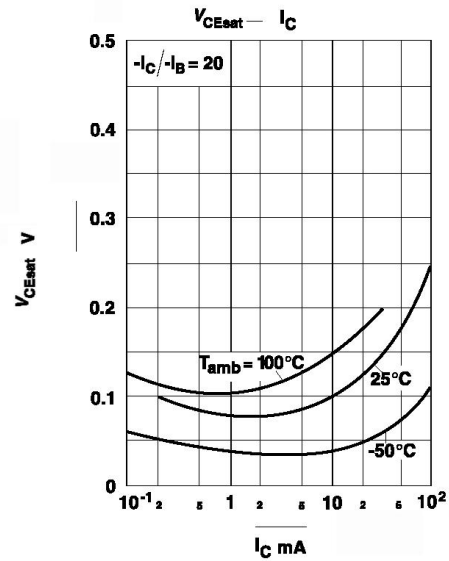
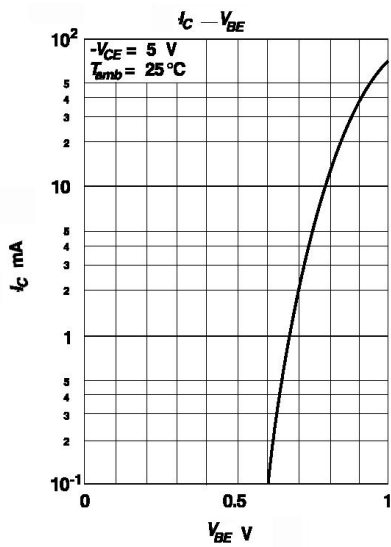
极限参数 / Absolute Maximum Ratings(Ta=25°C)

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Collector to Base Voltage	V_{CBO}	-30	V
Collector to Emitter Voltage	V_{CEO}	-30	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-100	mA
Collector Power Dissipation	P_C	350	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	55~150	°C

电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=-10mA$ $I_B=0$	-30			V
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=-10\mu A$ $I_E=0$	-30			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=-10\mu A$ $I_C=0$	-5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-30V$ $I_E=0$			-0.015	μA
DC Current Gain	h_{FE}	$V_{CE}=-5.0V$ $I_C=-2.0mA$	125		475	
Collector to Emitter Saturation Voltage	$V_{CE(sat)(1)}$	$I_C=-10mA$ $I_B=-0.5mA$		-0.075	-0.3	V
	$V_{CE(sat)(2)}$	$I_C=-100mA$ $I_B=-5.0mA$		-0.25	-0.65	V
Base to Emitter Saturation Voltage	$V_{BE(sat)(1)}$	$I_C=-10mA$ $I_B=-0.5mA$		-0.7		V
	$V_{BE(sat)(2)}$	$I_C=-100mA$ $I_B=-5.0mA$		-0.85		V
Base to Emitter Voltage	$V_{BE(ON)(1)}$	$V_{CE}=-5.0V$ $I_C=-2.0mA$	-0.6	-0.65	-0.75	V
	$V_{BE(ON)(2)}$	$V_{CE}=-5.0V$ $I_C=-10mA$			-0.82	V
Transition Frequency	f_T	$V_{CE}=-5.0V$ $f=100MHz$ $I_C=-10mA$		150		MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=-10V$ $f=1.0MHz$ $I_E=0$		4.5		pF
Noise Figure	NF	$V_{CE}=-5.0V$ $R_g=10K\Omega$ $I_C=-200\mu A$ $f=1.0KHz$			4.0	dB

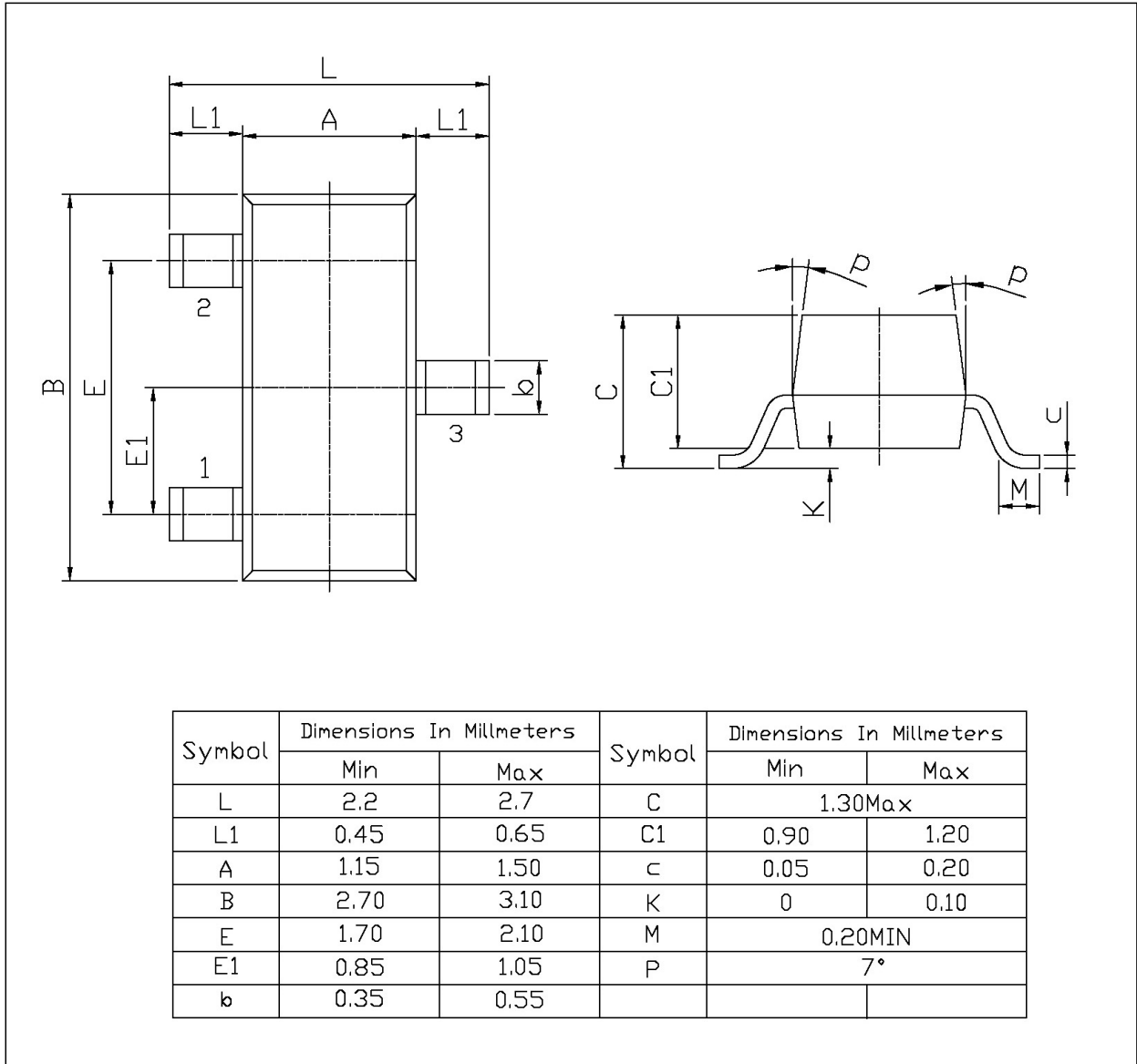
电参数曲线图 / Electrical Characteristic Curve



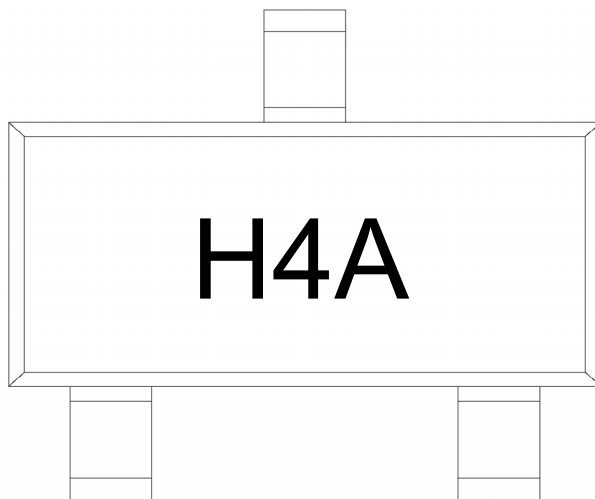
外形尺寸图 / Package Dimensions

SOT-23

单位: mm



印章说明 / Marking Instructions



说明：

H： 为公司代码

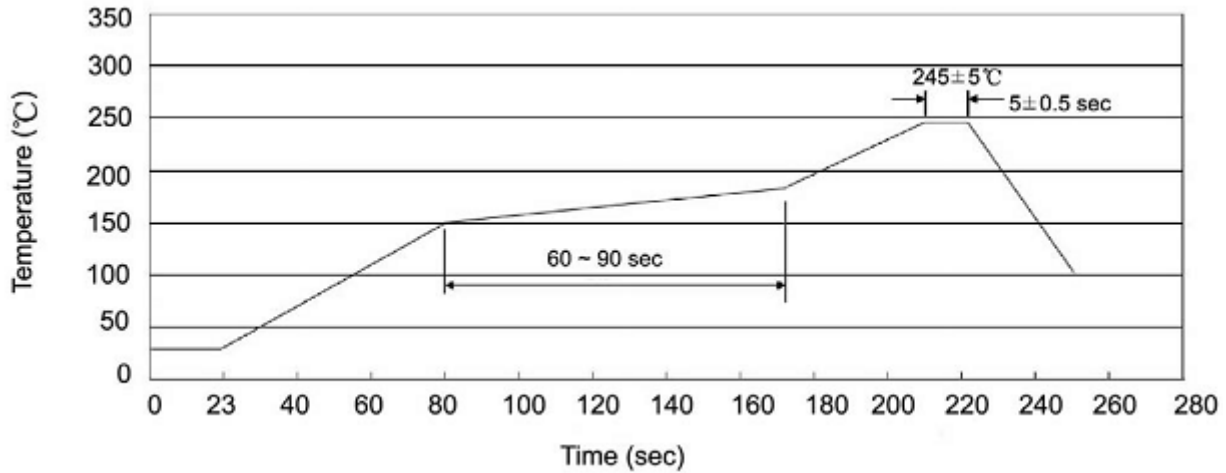
4A： 为型号代码

Note:

H: Company Code.

4A: Product Type Code

回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)



说明：

- 1、预热温度 25~150°C，时间 60~90sec;
- 2、峰值温度 245±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2~10°C/sec.

Note:

- 1.Preheating:25~150°C, Time:60~90sec.
- 2.Peak Temp.:245±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度：260±5°C

时间：10±1 sec.

Temp.:260±5°C

Time:10±1 sec

包装规格 / Packaging SPEC.

卷盘包装 / REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
SOT-23	3,000	10	30,000	8	240,000	7" x8	180×120×180	385×257×392

使用说明 / Notices